

1、Description

PNPN devices designed for high volume, line-powered consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in an inexpensive plastic **TO-92** package which is readily adaptable for use in automatic insertion equipment.

2、Features

- Sensitive gate allows triggering by micro-controllers and other logic circuits
- Blocking voltage to 600 thru 800 volts
- On-state RMS current to 1A RMS at 80°C
- Ultra low gate trigger current
- Glass-Passivated Surface for Reliability and Uniformity

3、Pinning information

PIN	Description	Simplified outline	Symbol
1	Cathode (K)	 TO-92	
2	Gate (G)		
3	Anode (A)		

4、Quick reference data

SYMBOL	PARAMETER	MAX	UNIT
V_{DRM} V_{RRM}	Repetitive peak off-state voltages	600	V
$I_T(RMS)$	RMS on-state current	1	A
I_{TSM}	Non-repetitive peak on-state current	10	A
I_{GT}	Gate trigger current	200	μ A

5、Thermal characteristics

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$R_{th\ j-mb}$	Thermal resistance, -- Junction to Case --Junction to Ambient		-	-	75 200	°C/W °C/W
T_L	Lead Solder Temperature	<1/16" from case, 10 secs max	-	260	-	°C

6. Limiting value

Limiting values in accordance with the Maximum System(IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{DRM}	Repetitive peak off-state voltages		-	600	V
V _{RRM}			-	1	A
I _{T(RMS)}	RMS on-state current		-		
I _{TSM}	Non-repetitive peak on-state current	1/2 Cycle,Sine Wave ,60HZ,T _j =25°C	-	10	A
I ² t	I ² t for fusing	T _j =-40 to +110°C(t=8.3ms)	-	0.415	A ² s
dI _T /dt	Repetitive rate of rise of on-state current after triggering	I _{TM} = 2 A; I _G = 10mA; dI _G /dt = 0.2 A/s	-	50	A/μs
I _{GM}	Peak gate current	TA=25°C, Pulse Width<=1.0us	-	1	A
V _{GM}	Peak gate voltage		-	5	V
V _{RGM}	Peak reverse gate voltage	TA=25°C, Pulse Width<=1.0us	-	5.0	V
P _{GM}	Peak gate power	TA=25°C, Pulse Width<=1.0us	-	1	W
P _{G(AV)}	Average gate power	TA=25°C,t<=8.3ms	-	0.1	W
T _{stg}	Storage temperature		-40	150	°C
T _j	Operating junction temperature		-40	110	°C

7. Characteristics

T_j = 25°C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
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Static characteristics

I _{DRM} , I _{RRM}	Peak Repetitive Forward Or Reverse Blocking Current	VD=Rated V _{DRM} and V _{RRM} , R _{GK} =1KΩ TC=25°C TC=110°C	-	-	10 100	μA μA
I _{GT}	Gate trigger current	VAK=7.0 Vdc,RL=100 Ohms	-	30	200	μA
I _L	Latching current	V _{AK} =7.0 Vdc,I _G =200μA TC=25°C TC=- 40°C	-	0.3 -	5 10	mA mA
I _H	Holding current	VD=7.0 Vdc, Initiating Current=20mA TC=25°C TC=- 40°C	-	0.2 -	1.0 10	mA mA
V _{TM}	On-state voltage	ITM=1.0 A Peak; @ TA=25°C	-	-	1.5	V
V _{GT}	Gate trigger voltage	V _{AK} =7.0 Vdc,,RL=100 Ohms TC=25°C TC=- 40°C	-	0.62 -	0.7 1.2	V V

Dynamic Characteristics

dv/dt	Critical rate of rise of off-state voltage	VD=Rated V _{DRM} ,Exponential Waveform, R _{GK} =1KΩ, T _j =110°C	-	20	35	V/μs
di/dt	Critical Rate-of-Rise of Off State Current	Ipk=20A;Pw=10μsec; dI/dt=1A/μsec,lgt=20 mA	-	-	50	μs

8、Electrical Characteristics Curve

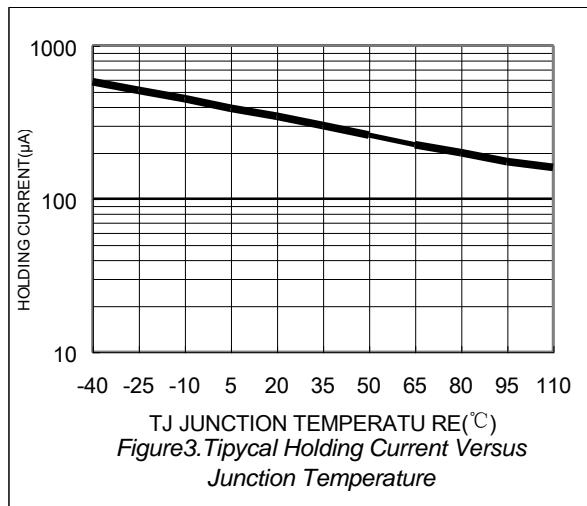
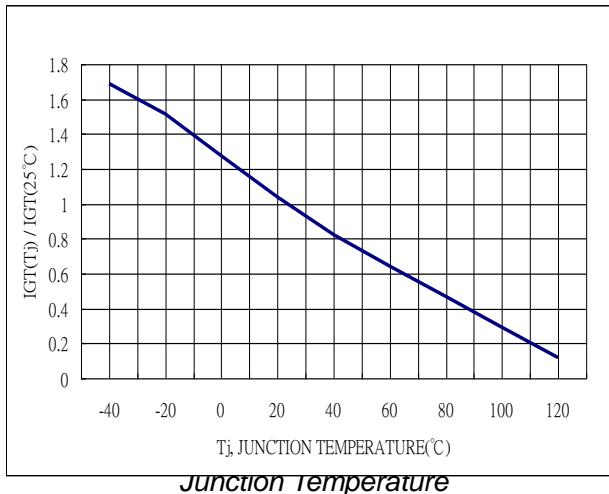


Figure 3.Typical Holding Current Versus Junction Temperature

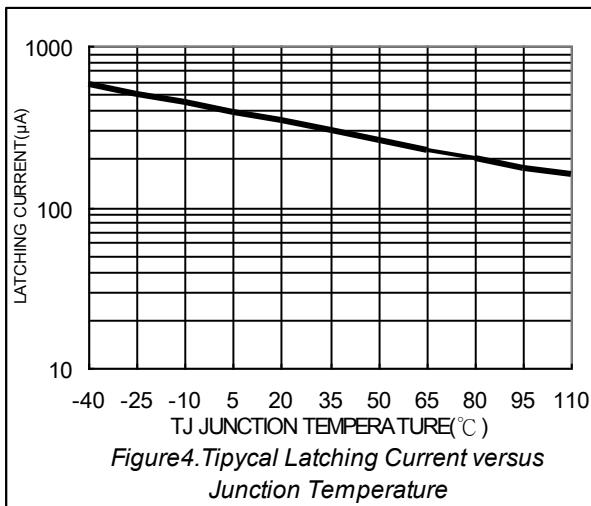


Figure 4.Typical Latching Current versus Junction Temperature

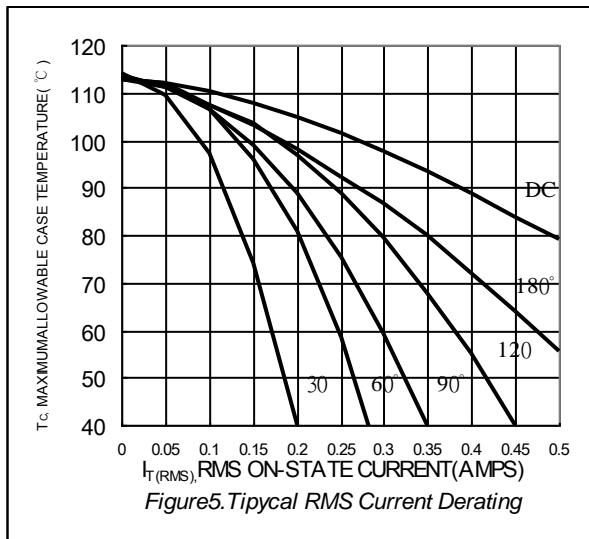


Figure 5.Typical RMS Current Derating

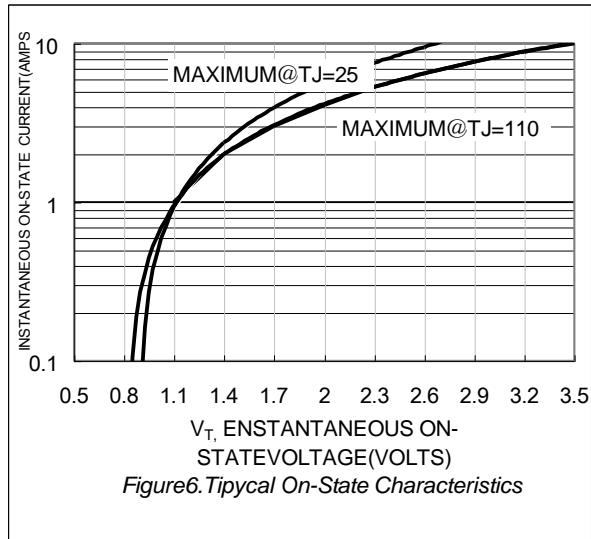
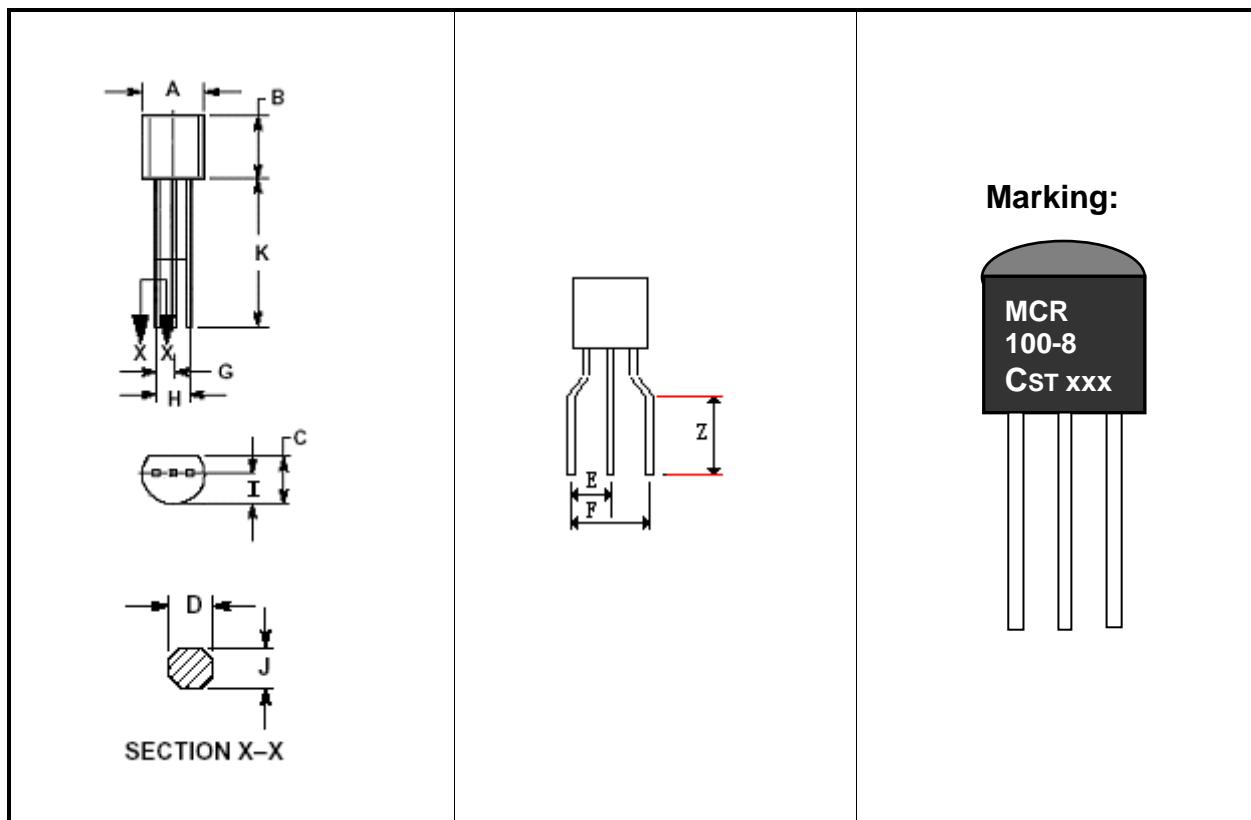


Figure 6.Typical On-State Characteristics

9、Package outline(TO-92)



DIM	Inches			Millimeters		
	Min	Type	Max	Min	Type	Max
A	0.175	-	0.205	4.45	-	5.20
B	0.170	-	0.210	4.32	-	5.33
C	0.134	-	0.142	3.40	-	3.60
K	0.500	-	-	12.70	-	-
G	0.045	-	0.055	1.14	-	1.39
H	0.095	-	0.105	2.41	-	2.67
I	0.080	-	0.105	2.04	-	2.66
D	0.016	-	0.021	0.41	-	0.53
J	0.012	-	0.018	0.30	-	0.45
E	0.08	-	0.112	2.15	-	2.85
F	0.179	-	0.215	4.55	-	5.45
Z	0.118	-	-	3.00	-	-

CST